Central™
Semiconductor Corp.

PROCESS CPD05

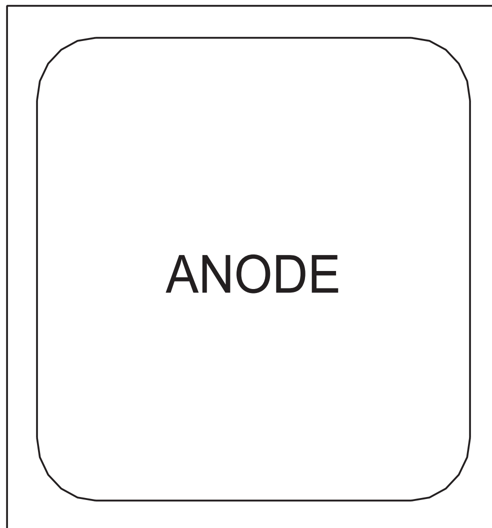
General Purpose Rectifier

1 Amp Glass Passivated Rectifier Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	50 x 50 MILS
Die Thickness	9.5 MILS
Anode Bonding Pad Area	34 x 34 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 4 INCH WAFER
4,520

PRINCIPAL DEVICE TYPES
1N3611 thru 1N3614
1N4001 thru 1N4007
1N4245 thru 1N4249
1N5059 thru 1N5062
1N5391 thru 1N5399
1N5614 thru 1N5622
CMR1-02 Series
CMR1-02M Series

The Typical Electrical Characteristics data for this chip is currently being revised.

For the latest updated data for this Chip Process, please visit our website at:

www.centralsemi.com/chip

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R1 (1-August 2002)